



TO-92S Plastic-Encapsulate Transistors

2SA608S TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM} : 300 \text{ mW (Tamb=25}^\circ\text{C)}$$

Collector current

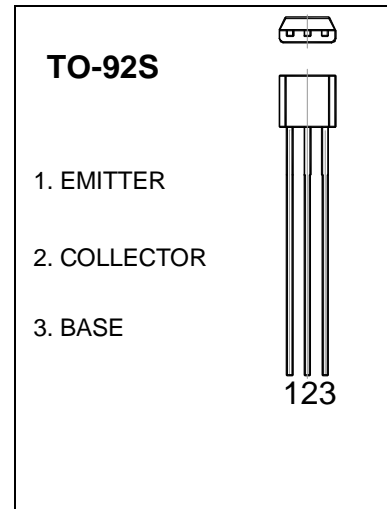
$$I_{CM} : -100 \text{ mA}$$

Collector-base voltage

$$V_{(BR)CBO} : -40 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-30			V
Emitter-Base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-25\text{V}, I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$			-1	μA
DC current gain	h_{FE}	$V_{CE}=-6\text{V}, I_C=-1\text{mA}$	60		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.5	V
Transition frequency	f_T	$V_{CE}=-6\text{V}, I_C=-10\text{mA}$		180		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-6\text{V}, f=1\text{MHz}$		7		pF

CLASSIFICATION OF h_{FE}

Rank	D	E	F	G
Range	60-120	100-200	160-320	280-560